MBR6045PT

Switch-mode Power Rectifier

Features and Benefits

- Low Forward Voltage
- Low Power Loss/High Efficiency
- High Surge Capacity
- 175°C Operating Junction Temperature
- 60 A Total (30 A Per Diode Leg)
- Pb-Free Packages are Available*

Applications

- Power Supply Output Rectification
- Power Management
- Instrumentation

Mechanical Characteristics

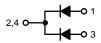
- Case: Epoxy, Molded
- Epoxy Meets UL 94, V-0 @ 0.125 in
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperatures for Soldering Purposes: 260°C Max. for 10 Seconds
- ESD Rating: Human Body Model 3B Machine Model C

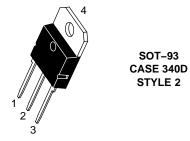


ON Semiconductor®

http://onsemi.com

SCHOTTKY BARRIER RECTIFIER 60 AMPERES 45 VOLTS





MARKING DIAGRAM



MBR6045PT =

= Device Code

A Y = Assembly Location

WW

= Year

G

Work WeekPb-Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
MBR6045PT	SOT-93	30 Units/Rail
MBR6045PTG	SOT-93 (Pb-Free)	30 Units/Rail

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MBR6045PT

MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	VRRM VRWM VR	45	V
Average Rectified Forward Current (Rated V _R , T _C = 125°C) Per Diode Per Device	I _{F(AV)}	30 60	А
Peak Repetitive Forward Current, (Rated V _R , Square Wave, 20 kHz @ T _C = 90°C) Per Diode	I _{FRM}	60	А
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I _{FSM}	500	А
Peak Repetitive Reverse Current (2.0 μs, 1.0 kHz)	I _{RRM}	2.0	Α
Storage Temperature Range	T _{stg}	-65 to +175	°C
Operating Junction Temperature (Note 1)	TJ	-65 to +175	°C
Peak Surge Junction Temperature (Forward Current Applied)		175	°C
Voltage Rate of Change	dv/dt	10,000	V/μs

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

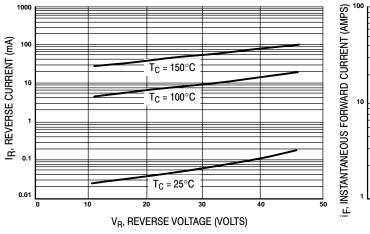
Characteristic	Conditions	Symbol	Max	Unit
Maximum Thermal Resistance, Junction-to-Case	Min. Pad	$R_{\theta JC}$	1.0	°C/W
Maximum Thermal Resistance, Junction-to-Ambient	Min. Pad	$R_{\theta JA}$	60	

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Typical	Max	Unit
Instantaneous Forward Voltage (Note 2)	VF	- - -	0.55 0.51 0.70	0.62 0.55 0.75	V
Instantaneous Reverse Current (Note 2) (Rated dc Voltage, Tj = 25°C) (Rated dc Voltage, Tj = 125°C)	i _R	_ _	0.2 35	1.0 50	mA

^{2.} Pulse Test: Pulse Width = 300 $\mu s, \, Duty \, Cycle \leq 2.0\%$

TYPICAL ELECTRICAL CHARACTERISTICS



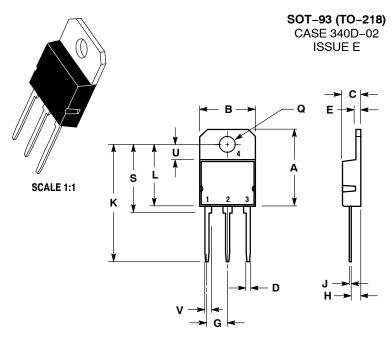
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Figure 1. Typical Reverse Current

Figure 2. Typical Forward Voltage

^{1.} The heat generated must be less than the thermal conductivity from Junction–to–Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.





STYLE 1: PIN 1. BASE

2. COLLECTOR 3. EMITTER

COLLECTOR

STYLE 2: PIN 1. ANODE

CATHODE
 ANODE

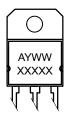
4. CATHODE

DATE 03 JAN 2002

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α		20.35		0.801
В	14.70	15.20	0.579	0.598
С	4.70	4.90	0.185	0.193
D	1.10	1.30	0.043	0.051
E	1.17	1.37	0.046	0.054
G	5.40	5.55	0.213	0.219
Н	2.00	3.00	0.079	0.118
J	0.50	0.78	0.020	0.031
K	31.00	REF	1.220	REF
L		16.20		0.638
Q	4.00	4.10	0.158	0.161
S	17.80	18.20	0.701	0.717
U	4.00	4.00 REF		REF
V	1.75 REF		0.0)69

GENERIC MARKING DIAGRAM*



= Assembly Location

= Year WW = Work Week XXXXX = Device Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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